



2828

~~STATEMENT~~ BY APPLICANT

OCT 15 2002

PATENT & TRADEMARK OFFICE

RECEIVED  
OCT 18 2002  
TECHNOLOGY CENTER 2800

Examiner Initials	Foreign Patent Document		Country	Date of Publication (MM-DD-YYYY)	Translation	
	Number	Kind Code (if known)			Yes	no

Examiner Initials,	Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		
JD	T. Nagatomo, et al., "Properties of Ga <sub>1-x</sub> In <sub>x</sub> N Films Prepared by MOVPE", Japanese Journal of Applied Physics, Vol. 28, No. 9, August, 1989, pp. L1334-L1336 Blue Device Development Story (P1-6 and P10, ELECTRONICS, April 1999 issue) (with English Translation)		
JD	K. Osamura, et al., "Fundamental Absorption Edge in GaN, InN and Their Alloys", Solid State Communications, Vol. 11, 1972, pp. 617-621 (No matter)		
JD	S. Yoshida, et al., "Properties of Al <sub>x</sub> Ga <sub>1-x</sub> N Films Prepared by Reactive Molecular Beam Epitaxy", J. Appl. Phys., Vol. 53, No. 10, October 1982		
JD	K. Osamura, et al., "Preparation and Optical Properties of Ga <sub>1-x</sub> In <sub>x</sub> N Thin Films", Journal of Applied Physics, Vol. 46, No. 8, August 1975		
JD	Y. Koide, et al., "Energy Band-Gap Bowing Parameter in an Al <sub>x</sub> Ga <sub>1-x</sub> N Alloy", J. Appl. Phys. Vol. 61, No. 9, 1 May 1987		
JD	T. Awasaki, et al., "MOVPE Growth Of High Quality Al <sub>x</sub> Ga <sub>1-x</sub> N/Ga <sub>y</sub> In <sub>1-y</sub> N (x > 0, y < 1) Heterostructures for Short Wavelength Light Emitter", Mat. Res. So. Symp. Pro., Vol. 339, 1994		pages 4
JD	L. Hrivnak, "Band Gap, Effective Masses, and Band Offsets in Lattice Matched Heterojunctions", Phys. Stat. Sol. (a), Vol. 128, K.89, 1991		
Examiner Signature	[Signature]		Date Considered 10/23/02

(05/01)